

1002MP

2 Watts, 35 Volts Pulsed Avionics at 960-1215 MHz

GENERAL DESCRIPTION

The 1002MP is a COMMON BASE transistor capable of providing 2 Watts of pulsed RF output power in the band 960 to 1215 MHz. This transistor is specifically designed for pulsed Avionics amplifier applications. It utilizes gold metallization and low thermal resistance packaging to provide high reliability and supreme ruggedness.

CASE OUTLINE 55FW-1

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

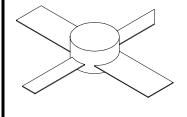
Device Dissipation @ 25°C 7 W

Maximum Voltage and Current

 $\begin{array}{lll} \mbox{Collector to Base Voltage } (\mbox{BV}_{ces}) & 50 \ \mbox{V} \\ \mbox{Emitter to Base Voltage } (\mbox{BV}_{ebo}) & 3.5 \ \mbox{V} \\ \mbox{Collector Current } (\mbox{I}_c) & 250 \ \mbox{mA} \\ \end{array}$

Maximum Temperatures

Storage Temperature $-40 \text{ to } +150 \text{ }^{\circ}\text{C}$ Operating Junction Temperature $+200 \text{ }^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Output	F = 1150 MHz	2.0	4		W
P_{in}	Power Input				0.3	W
P_{g}	Power Gain	$V_{cc} = 35 \text{ Volts}$	8.24	11		dB
$\eta_{\rm c}$	Collector Efficiency	Pulse width = $20 \mu s$		45		%
VSWR	Load Mismatch Tolerance	LTDF = 1%			10:1	

FUNCTIONAL CHARACTERISTICS @ 25°C

$\mathrm{BV}_{\mathrm{ebo}}$	Emitter to Base Breakdown	Ie = 1 mA	3.5			V
$\mathrm{BV}_{\mathrm{ces}}$	Collector to Emitter Breakdown	Ic = 5 mA	50			V
h_{FE}	DC – Current Gain	Vce = 5V, $Ic = 100 mA$	20			
C_{ob}	Capacitance	Vcb=35V, f=1MHz		2.2	5.0	pF
θjc ¹	Thermal Resistance				25	°C/W

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